

DESCRIPTION

The GLF72501 Load Switch is a fully integrated 2 A NMOS load switch with I_QSmart™ advanced technology. The device is targeted for the mobile computing and data storage markets as a high performance, low cost solution for load switch applications.

The GLF72501 has a constant low on-resistance of 32 mΩ at room temperature. The fixed rise time helps prevent undesirable inrush current when turned on and the internal EN pin pulldown resistor ensures the device remains in the shutdown mode when disabled.

The GLF72501 is available in a wafer level chip scale package (WLCSP) measuring 0.77 mm x 0.77 mm x 0.46 mm with a 0.4 mm pitch. This allows the user to save board space and increase cost savings.

The GLF72501 features a reverse current blocking protection. When the GLF72501 is disabled, it prevents reverse current flowing from the output to the input source.

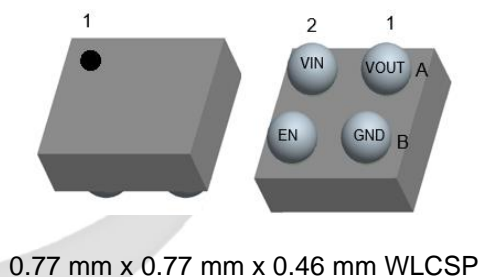
FEATURES

- Supply Voltage Range : 0.8 V to 3.6 V
- Low R_{ON} : 32 mΩ Typ at Supply Voltage Range
- I_{OUT} Max : 2 A
- Ultra-Low I_Q :
 - 200 nA Typ at 0.8 V_{IN}
 - 180 nA Typ at 1.0 V_{IN}
 - 170 nA Typ at 1.2 V_{IN}
- Integrated Slew Rate Control Driver
- Reverse Current Blocking Protection When Disabled
- Internal EN Pull-Down Resistor
- Integrated Output Discharge Switch
- HBM : 6 kV, CDM : 2 kV

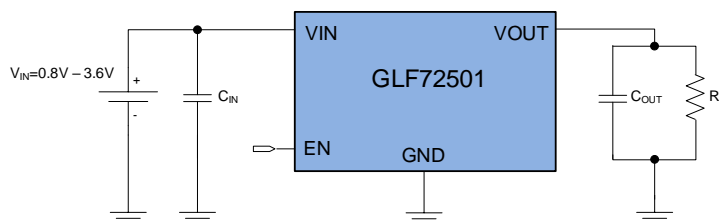
APPLICATIONS

- Wearables
- Data Storage, SSD
- Low Power Subsystems

PACKAGE



APPLICATION DIAGRAM



ALTERNATE DEVICE OPTIONS

Part Number	Top Mark	R _{ON} Typ. at V _{IN} Range	Output Discharge	EN Activity
GLF72501	G	32 mΩ	80 Ω	High

FUNCTIONAL BLOCK DIAGRAM

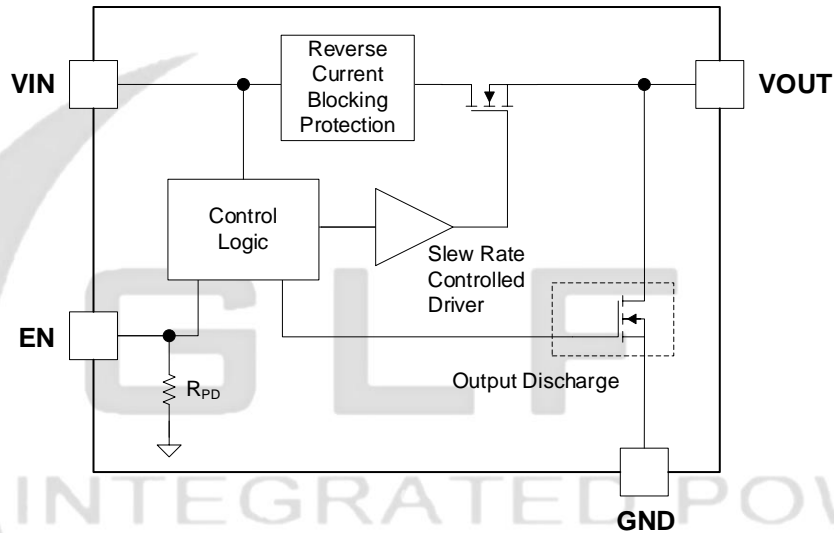
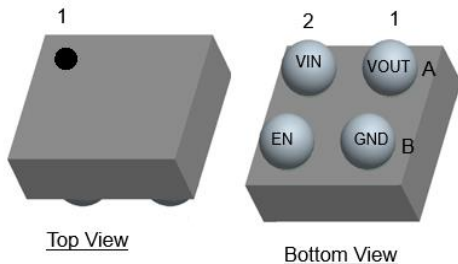


Figure 1. Functional Block Diagram

PIN CONFIGURATION

PIN DEFINITION



Pin #	Name	Description
A1	V _{OUT}	Switch Output
A2	V _{IN}	Switch Input. Supply Voltage for IC
B1	GND	Ground
B2	EN	Enable to control the switch

Figure 2. 0.77 mm x 0.77 mm x 0.46 mm WLCSP

ABSOLUTE MAXIMUM RATINGS

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter		Min.	Max.	Unit
V _{IN}	V _{IN} , V _{OUT} , V _{EN} to GND		-0.3	4	V
I _{OUT}	Maximum Continuous Switch Current			2	A
P _D	Power Dissipation at T _A = 25°C			1.2	W
T _{STG}	Storage Junction Temperature		-65	150	°C
T _A	Operating Temperature Range		-40	85	°C
θ _{JA}	Thermal Resistance, Junction to Ambient			85	°C/W
ESD	Electrostatic Discharge Capability	Human Body Model, JESD22-A114	6		kV
		Charged Device Model, JESD22-C101	2		

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min.	Max.	Unit
V _{IN}	Supply Voltage	0.8	3.6	V
T _A	Ambient Operating Temperature	-40	+85	°C

ELECTRICAL CHARACTERISTICS

$V_{IN} = 0.8 \text{ V}$ to 3.6 V and $T_A = 25 \text{ }^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
Basic Operation						
I_Q	Quiescent Current	EN = Enable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 0.8 \text{ V}$		0.20		μA
		EN = Enable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 1.0 \text{ V}$		0.18		
		EN = Enable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 1.2 \text{ V}$		0.17		
		EN = Enable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 2.5 \text{ V}$		3.2		
		EN = Enable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 3.0 \text{ V}$		6.8		
		EN = Enable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 3.3 \text{ V}$		10.3		
		EN = Enable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 3.6 \text{ V}$		14.3		
		EN = Enable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 3.6 \text{ V}$, $T_A = 85 \text{ }^{\circ}\text{C}$		28		
I_{SD}	Shutdown Current	EN = Disable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 0.8 \text{ V}$		4		nA
		EN = Disable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 1.0 \text{ V}$		6		
		EN = Disable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 1.2 \text{ V}$		7		
		EN = Disable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 2.5 \text{ V}$		40		
		EN = Disable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 3.0 \text{ V}$		170		
		EN = Disable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 3.3 \text{ V}$		500		
		EN = Disable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 3.6 \text{ V}$		630		
		EN = Disable, $I_{OUT} = 0 \text{ mA}$, $V_{IN} = 3.6 \text{ V}$, $T_A = 85 \text{ }^{\circ}\text{C}$		965		
R_{ON}	On-Resistance	$V_{IN} = 0.8 \text{ V}$ to 3.6 V $I_{OUT} = 300 \text{ mA}$	$T_A = 25 \text{ }^{\circ}\text{C}$	32	38	$\text{m}\Omega$
			$T_A = 85 \text{ }^{\circ}\text{C}$	40	45	
V_{IH}	EN Input Logic High Voltage	$V_{IN} = 0.8 \text{ V} - 1.5 \text{ V}$	0.8			V
		$V_{IN} = 1.5 \text{ V} - 3.6 \text{ V}$	1.1			V
V_{IL}	EN Input Logic Low Voltage	$V_{IN} = 0.8 \text{ V} - 1.5 \text{ V}$			0.2	V
		$V_{IN} = 1.5 \text{ V} - 3.6 \text{ V}$			0.5	V
R_{EN}	EN pull down resistance	Internal Resistance		10		$\text{M}\Omega$
R_{DSC}	Output Discharge Resistance ⁽¹⁾	EN = GND		80		Ω

Notes: 1. Output discharge path is disabled when main switch is off.

ELECTRICAL CHARACTERISTICS

$V_{IN} = 0.8\text{ V}$ to 3.6 V and $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
Switching Characteristics ⁽²⁾						
t_{dON}	Turn-On Delay $R_{OUT} = 150\text{ }\Omega$, $C_{OUT} = 0.1\text{ }\mu\text{F}$	$V_{IN} = 0.8\text{ V}$		2300		μs
		$V_{IN} = 1.2\text{ V}$		290		
		$V_{IN} = 3.3\text{ V}$		145		
		$V_{IN} = 3.6\text{ V}$		130		
t_r	V_{OUT} Rise Time $R_{OUT} = 150\text{ }\Omega$, $C_{OUT} = 0.1\text{ }\mu\text{F}$	$V_{IN} = 0.8\text{ V}$		3300		
		$V_{IN} = 1.2\text{ V}$		480		
		$V_{IN} = 3.3\text{ V}$		390		
		$V_{IN} = 3.6\text{ V}$		400		
t_{dOFF}	Turn-Off Delay $R_{OUT} = 150\text{ }\Omega$, $C_{OUT} = 0.1\text{ }\mu\text{F}$	$V_{IN} = 0.8\text{ V}$		52		
		$V_{IN} = 1.2\text{ V}$		4		
		$V_{IN} = 3.3\text{ V}$		1		
		$V_{IN} = 3.6\text{ V}$		1		
t_f	V_{OUT} Fall Time $R_{OUT} = 150\text{ }\Omega$, $C_{OUT} = 0.1\text{ }\mu\text{F}$	$V_{IN} = 0.8\text{ V}$		25		
		$V_{IN} = 1.2\text{ V}$		14		
		$V_{IN} = 3.3\text{ V}$		11		
		$V_{IN} = 3.6\text{ V}$		11		

Notes: 2. By design; characterized, not production tested. $t_{ON} = t_{dON} + t_r$, $t_{OFF} = t_{dOFF} + t_f$

TIMING DIAGRAM

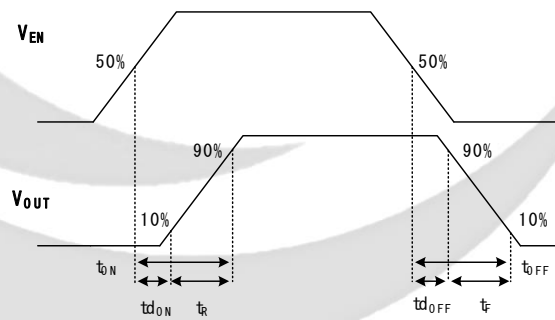


Figure 3. Timing Diagram

TYPICAL PERFORMANCE CHARACTERISTICS

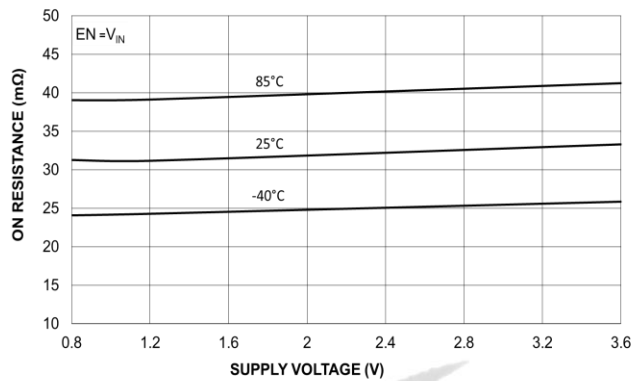


Figure 1. On-Resistance vs. Supply Voltage

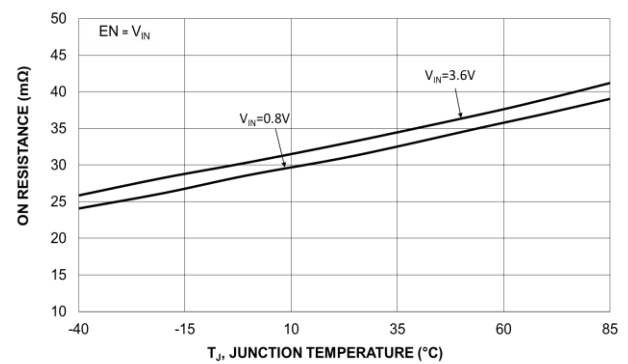


Figure 2. On-Resistance vs. Temperature

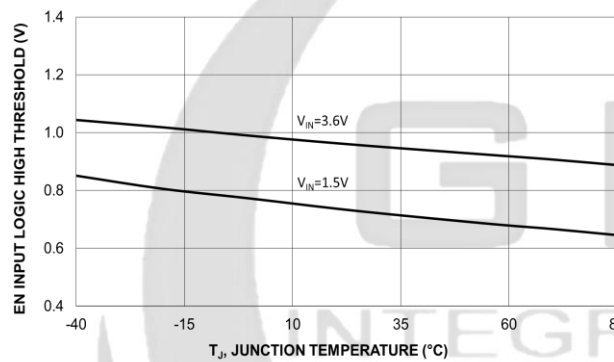


Figure 3. EN Input Logic High Threshold Vs. Temperature

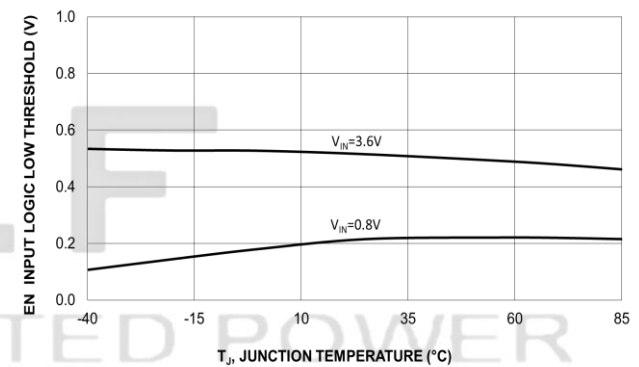


Figure 7. EN Input Logic Low Threshold Vs. Temperature

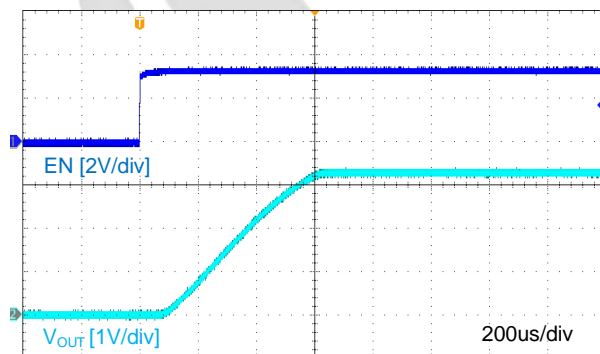


Figure 8. Turn-On Response

$V_{IN} = 3.3\text{ V}$, $C_{OUT} = 0.1\text{ }\mu\text{F}$, $R_L = 150\text{ }\Omega$

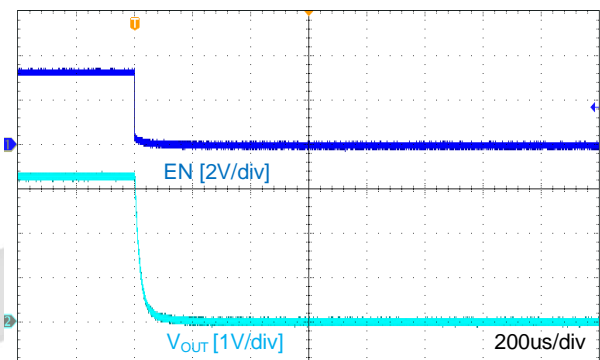


Figure 9. Turn-Off Response, GLF72511

$V_{IN} = 3.3\text{ V}$, $C_{OUT} = 0.1\text{ }\mu\text{F}$, $R_L = 150\text{ }\Omega$

APPLICATION INFORMATION

The GLF72501 is a fully integrated 2 A NMOS load switch with fixed slew rate control to limit the inrush current during turn on. Each device is capable of operating over a wide input range from 0.8 V to 3.6 V with very low on-resistance to reduce conduction loss. In the off state, these devices consume very low leakage current, avoiding unwanted standby current from the input power supply. The GLF72501 is available in the 0.77 mm x 0.77 mm x 0.46 mm wafer level chip scale package with four bumps at 0.4 mm pitch to save space in compact applications.

Input Capacitor

A capacitor is recommended to be placed close to the V_{IN} pin to reduce the voltage drop on the input power rail caused by transient inrush current at start-up. A higher input capacitor value can be used to further attenuate the input voltage drop.

Output Capacitor

An output capacitor is recommended to minimize voltage undershoot on the output pin during the transition when the switch is turned off. Undershoot can be caused by parasitic inductance from board traces or intentional load inductances. If load inductances do exist, use of an output capacitor can improve output voltage stability and system reliability. The C_{OUT} capacitor should be placed close to the VOUT and GND pins.

Reverse Current Blocking

The GLF72501 has a built-in reverse current blocking protection. When the device is disabled, the reverse current blocking protection is activated to prevent the reverse current from the Vout to the Vin source.

EN pin

The GLF72501 can be activated by EN pin high. Note that the EN pin has an internal pull-down resistor to maintain a reliable status without EN signal applied from an external controller.

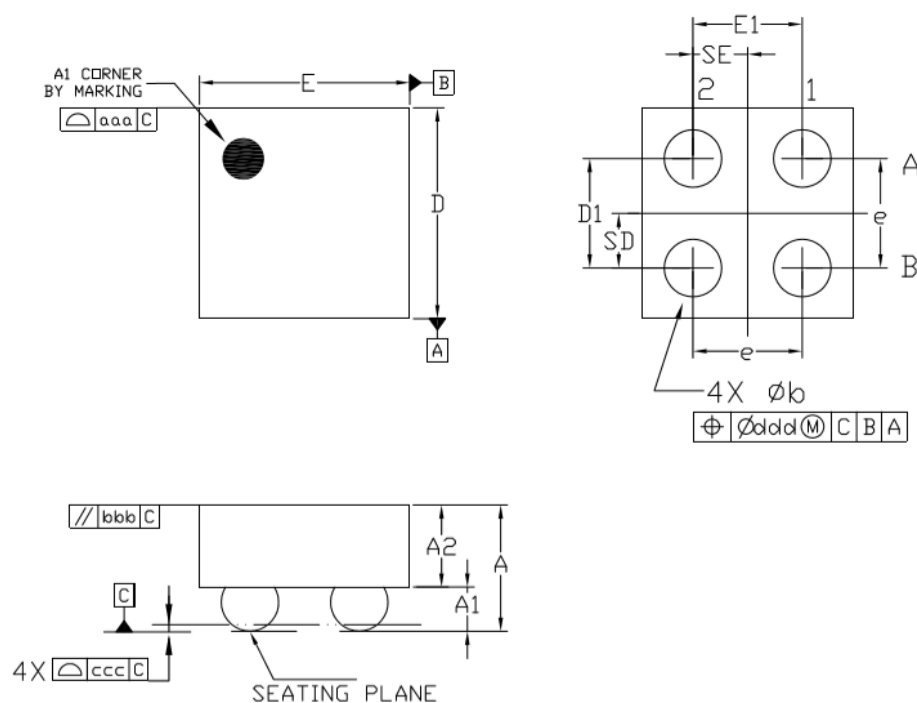
Output Discharge Function

The GLF72501 has an internal discharge N-channel FET switch on the VOUT node. When EN signal turns the main power FET to an off state, the N-channel switch turns on to discharge an output capacitor quickly.

Board Layout

All traces should be as short as possible to minimize parasitic inductance effect. Wide traces for VIN, VOUT, and GND will help reduce signal degradation and parasitic effects during dynamic operations as well as improve the thermal performance at high load current.

PACKAGE OUTLINE



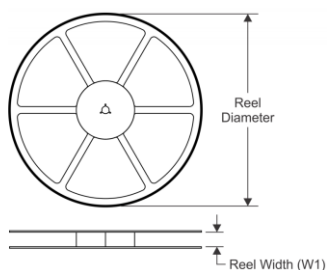
Dimensional Ref.			
REF.	Min.	Nom.	Max.
A	0.410	0.460	0.510
A1	0.135	0.160	0.185
A2	0.275	0.300	0.325
D	0.755	0.770	0.785
E	0.755	0.770	0.785
D1	0.350	0.400	0.450
E1	0.350	0.400	0.450
b	0.170	0.210	0.250
e	0.400 BSC		
SD	0.200 BSC		
SE	0.200 BSC		
Tol. of Form&Position			
aaa	0.10		
bbb	0.10		
ccc	0.05		
ddd	0.05		

Notes

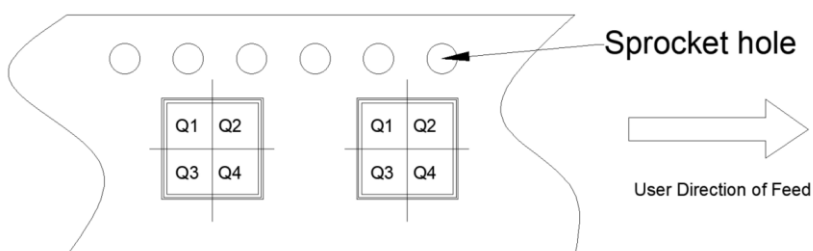
1. ALL DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.

TAPE AND REEL INFORMATION

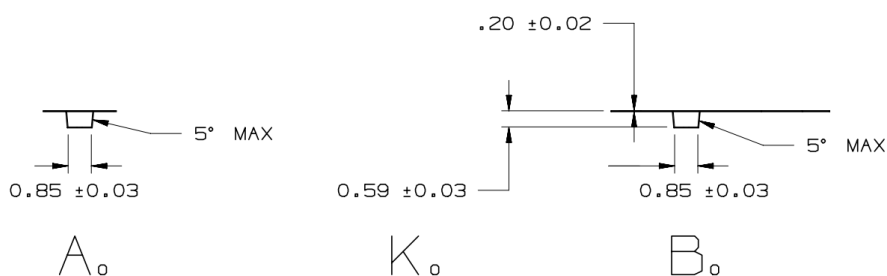
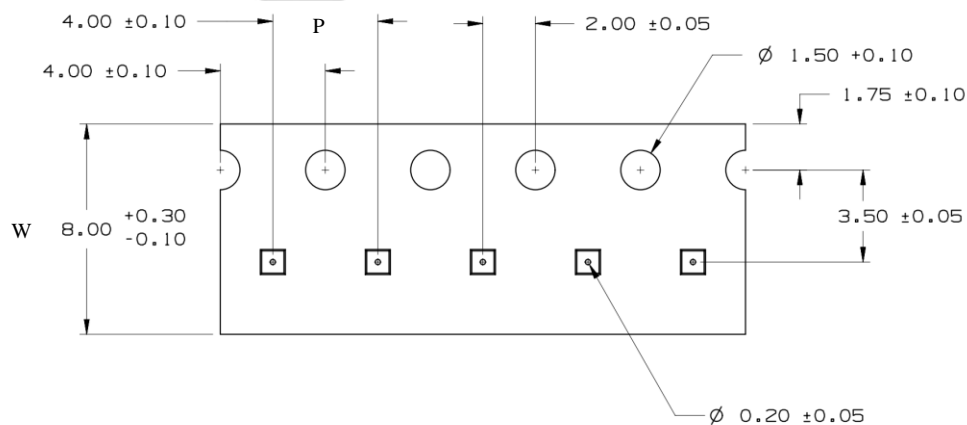
REEL DIMENSIONS



QUADRANT ASSIGNMENTS PIN 1 ORIENTATION TAPE



TAPE DIMENSIONS



Device	Package	Pins	SPQ	Reel Diameter(mm)	Reel Width W1	A0	B0	K0	P	W	Pin1
GLF72501	WLCSP	4	4000	180	9	0.85	0.85	0.59	4	8	Q1

Remark:

A0: Dimension designed to accommodate the component width

B0: Dimension designed to accommodate the component length

C0: Dimension designed to accommodate the component thickness

W: Overall width of the carrier tape

P: Pitch between successive cavity centers

SPECIFICATION DEFINITIONS

Document Type	Meaning	Product Status
Target Specification	This is a target specification intended to support exploration and discussion of critical needs for a proposed or target device. Spec limits including typical, minimum, and maximum values are desired, or target, limits. GLF reserves the right to change limits at any time without warning or notification. A target specification in no way guarantees future production of the device in question.	Design / Development
Preliminary Specification	This is a draft version of a product specification. The specification is still under internal review and subject to change. GLF reserves the right to change the specification at any time without warning or notification. A preliminary specification in no way guarantees future production of the device in question.	Qualification
Product Specification	This document represents the anticipated production performance characteristics of the device.	Production

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